



BTA410-600CT

3Q Hi-Com Triac

Rev. 1 — 15 March 2012

Product data sheet

1. Product profile

1.1 General description

Planar passivated high commutation three quadrant triac in a SOT78 (TO-220AB) plastic package intended for use in circuits where high static and dynamic dV/dt and high dI/dt can occur. This "series CT" triac will commute the full RMS current at the maximum rated junction temperature ($T_{j(max)} = 150\text{ }^{\circ}\text{C}$) without the aid of a snubber. It is used in applications where "high junction operating temperature capability" is required.

1.2 Features and benefits

- 3Q technology for improved noise immunity
- High commutation capability with maximum false trigger immunity
- High immunity to false turn-on by dV/dt
- High junction operating temperature capability
- High voltage capability
- Less sensitive gate for high noise immunity
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only

1.3 Applications

- Applications subject to high temperature
- Electronic thermostats (heating and cooling)
- Motor controls e.g. washing machines and vacuum cleaners
- Rectifier-fed DC inductive loads e.g. DC motors and solenoids

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	600	V
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25\text{ }^{\circ}\text{C}$; $t_p = 20\text{ ms}$; see Figure 4 ; see Figure 5	-	-	100	A
T_j	junction temperature		-	-	150	$^{\circ}\text{C}$
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 131\text{ }^{\circ}\text{C}$; see Figure 1 ; see Figure 2 ; see Figure 3	-	-	10	A

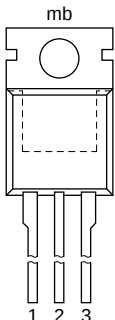
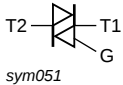


Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; see Figure 7	2	-	35	mA
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; see Figure 7	2	-	35	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; see Figure 7	2	-	35	mA
Dynamic Characteristics						
dV _D /dt	rate of rise of off-state voltage	V _{DM} = 402 V; T _j = 150 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit	500	-	-	V/μs
dI _{com} /dt	rate of change of commutating current	V _D = 400 V; T _j = 150 °C; I _{T(RMS)} = 10 A; dV _{com} /dt = 20 V/μs; (snubberless condition); gate open circuit	8	-	-	A/ms

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		
2	T2	main terminal 2		
3	G	gate		
mb	T2	mounting base; main terminal 2		

SOT78 (TO-220AB)

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BTA410-600CT	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	600	V
$I_{\text{T(RMS)}}$	RMS on-state current	full sine wave; $T_{\text{mb}} \leq 131\text{ }^{\circ}\text{C}$; see Figure 1 ; see Figure 2 ; see Figure 3	-	10	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{\text{J(init)}} = 25\text{ }^{\circ}\text{C}$; $t_{\text{p}} = 20\text{ ms}$; see Figure 4 ; see Figure 5	-	100	A
		full sine wave; $T_{\text{J(init)}} = 25\text{ }^{\circ}\text{C}$; $t_{\text{p}} = 16.7\text{ ms}$	-	110	A
I^2t	I^2t for fusing	$t_{\text{p}} = 10\text{ ms}$; sine-wave pulse	-	50	A^2s
di_{T}/dt	rate of rise of on-state current	$I_{\text{T}} = 20\text{ A}$; $I_{\text{G}} = 0.2\text{ A}$; $di_{\text{G}}/dt = 0.2\text{ A}/\mu\text{s}$	-	100	A/s
I_{GM}	peak gate current		-	2	A
P_{GM}	peak gate power		-	5	W
$P_{\text{G(AV)}}$	average gate power	over any 20 ms period	-	0.5	W
T_{stg}	storage temperature		-40	150	$^{\circ}\text{C}$
T_{J}	junction temperature		-	150	$^{\circ}\text{C}$

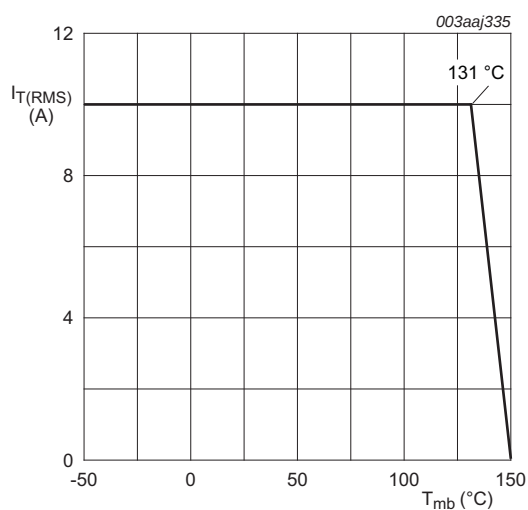


Fig 1. RMS on-state current as a function of mounting base temperature; maximum values

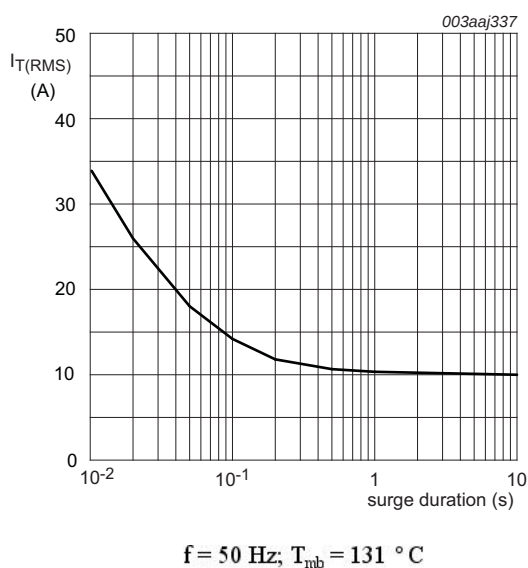


Fig 2. RMS on-state current as a function of surge duration; maximum values

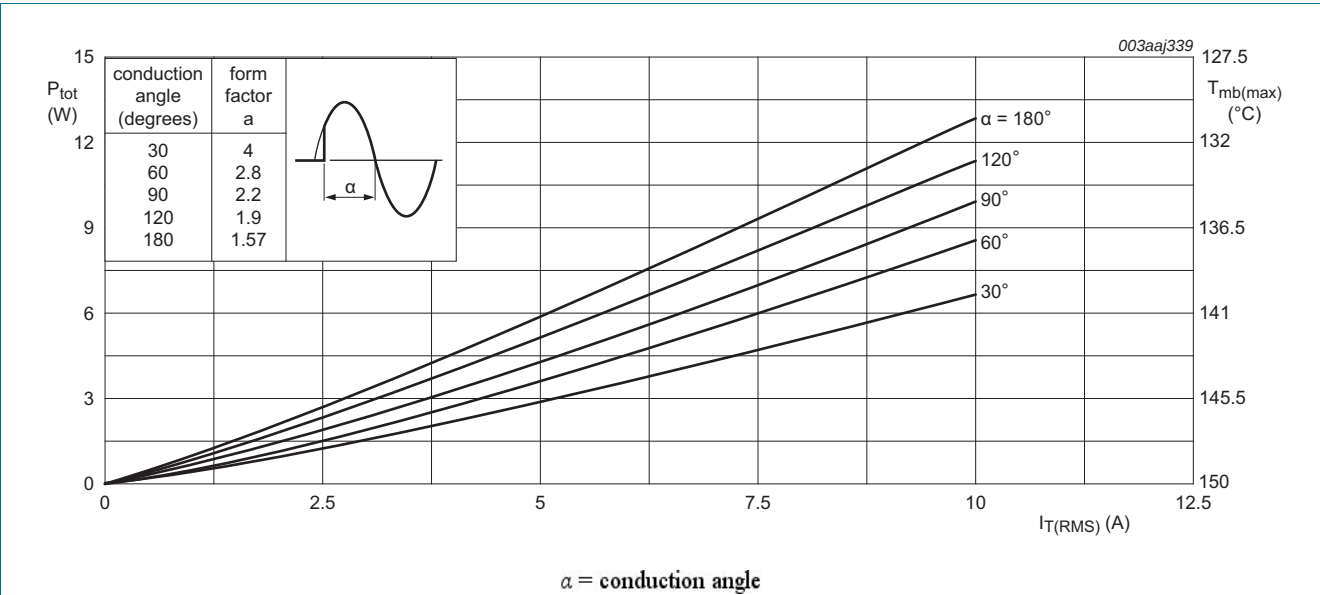


Fig 3. Total power dissipation as a function of RMS on-state current; maximum values

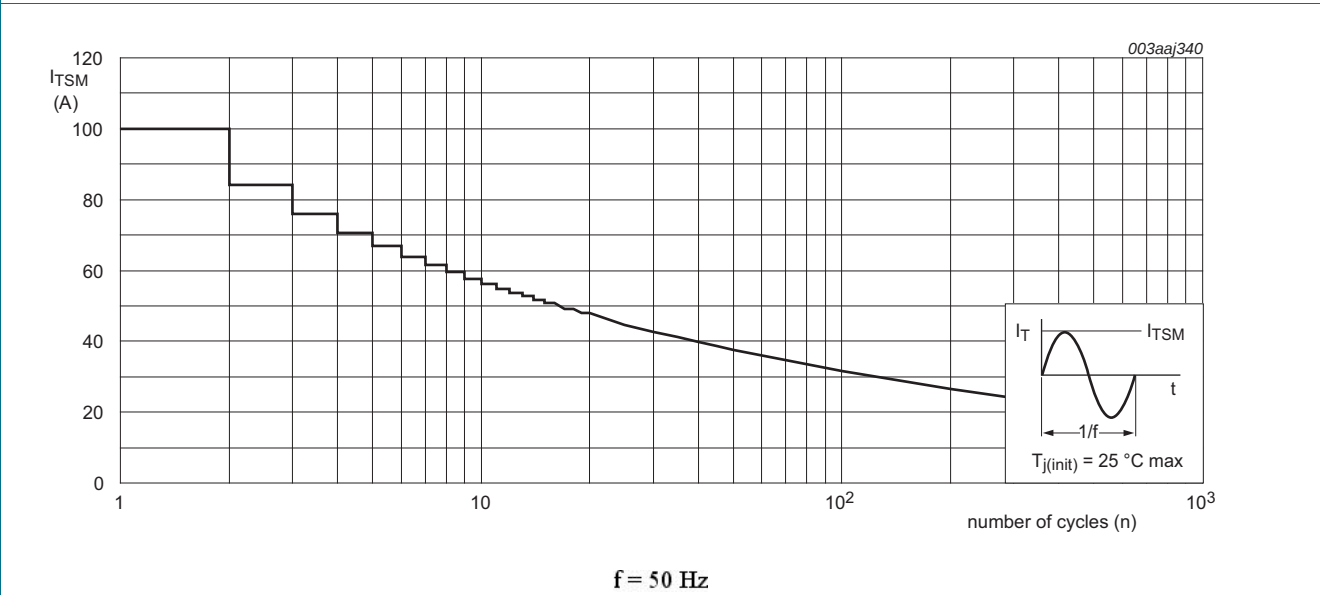


Fig 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

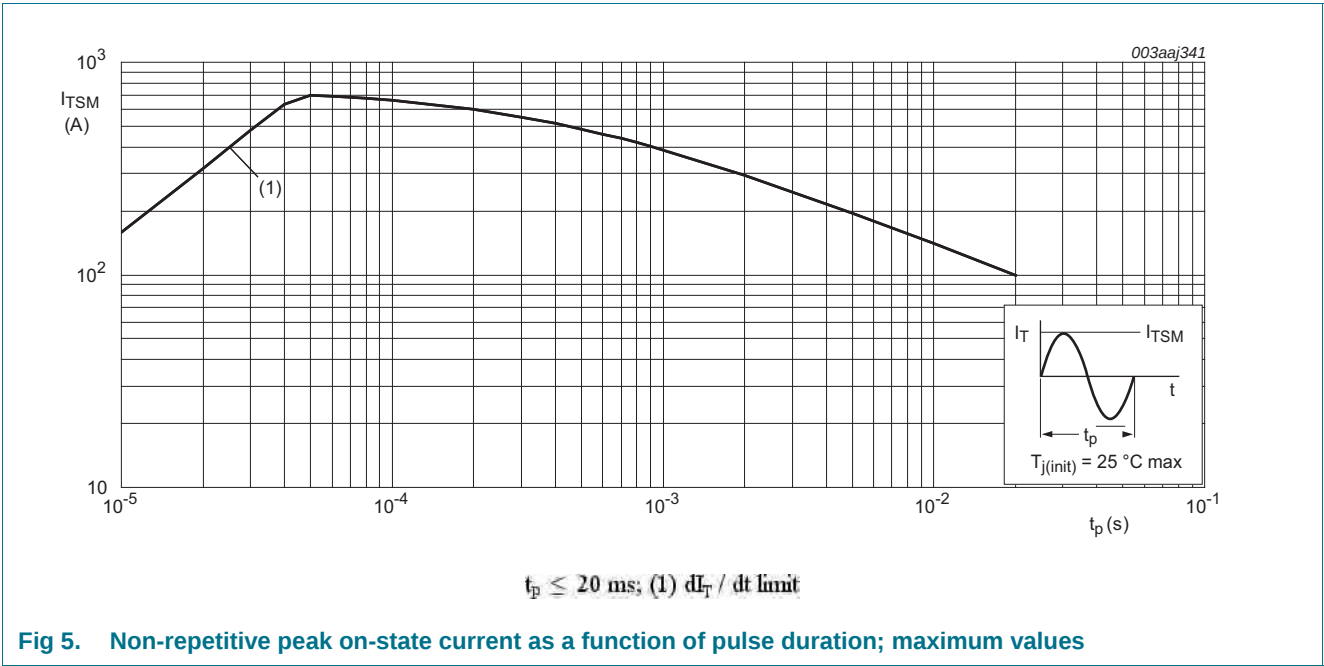
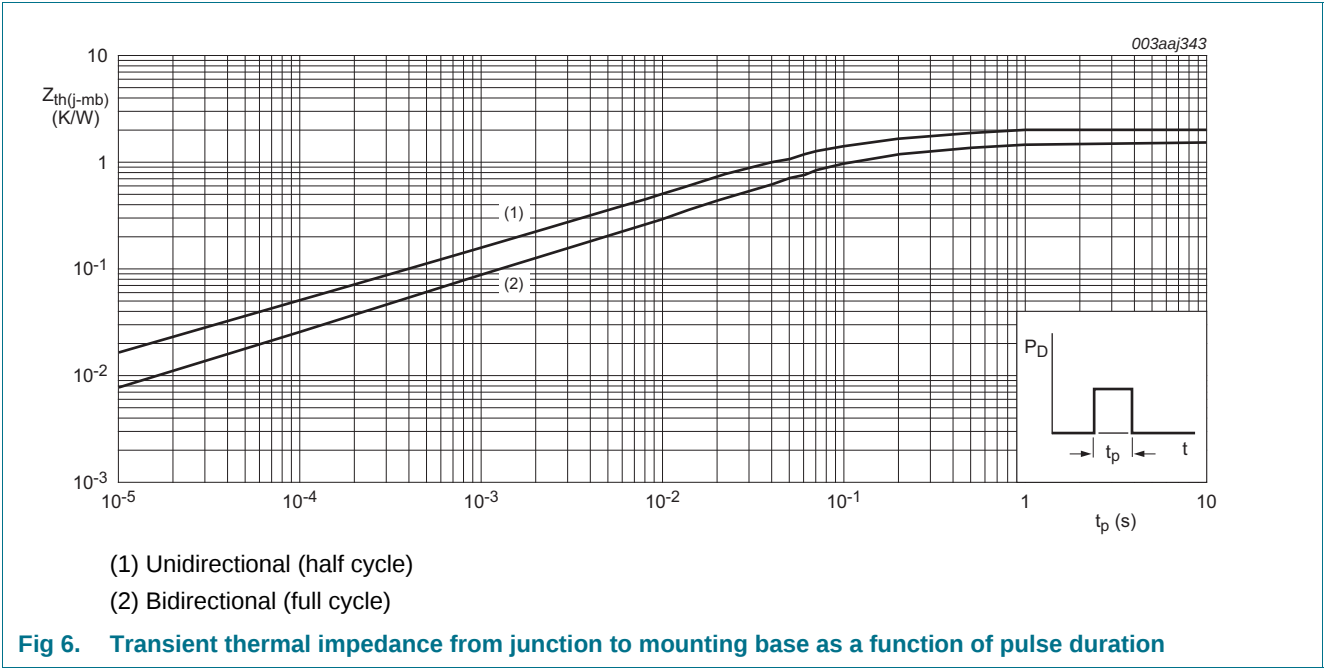


Fig 5. Non-repetitive peak on-state current as a function of pulse duration; maximum values

5. Thermal characteristics

Table 5. Thermal characteristics

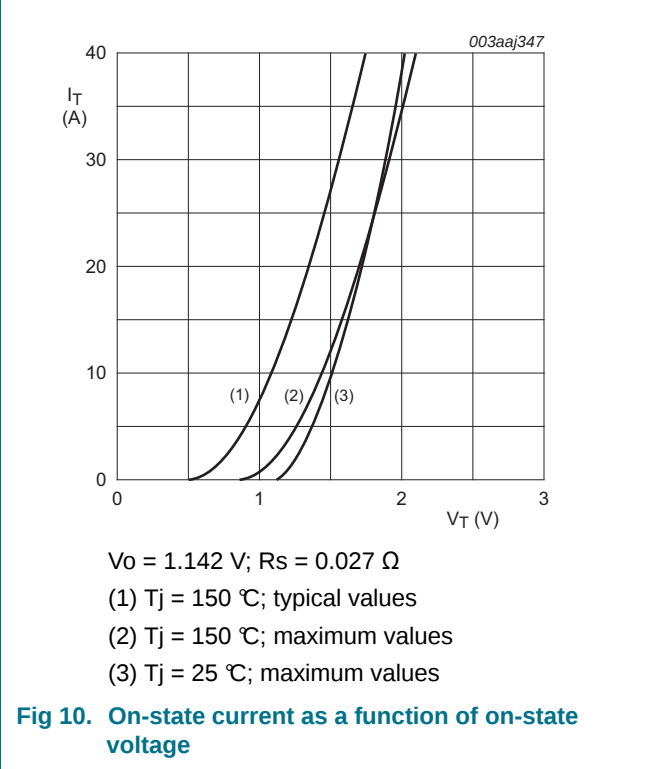
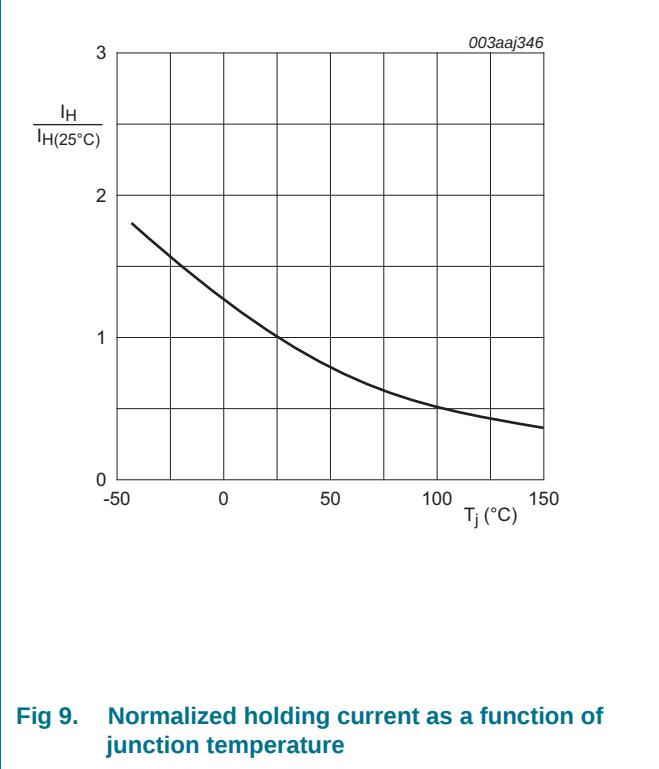
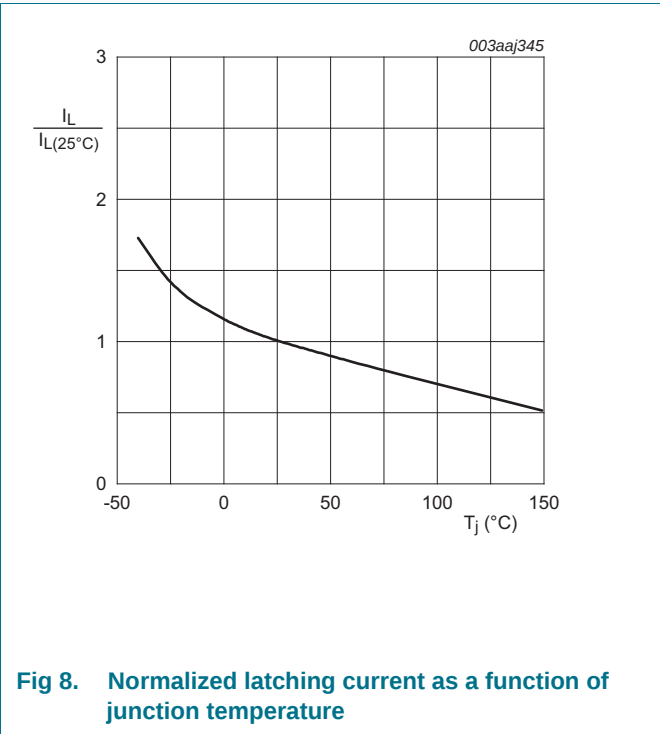
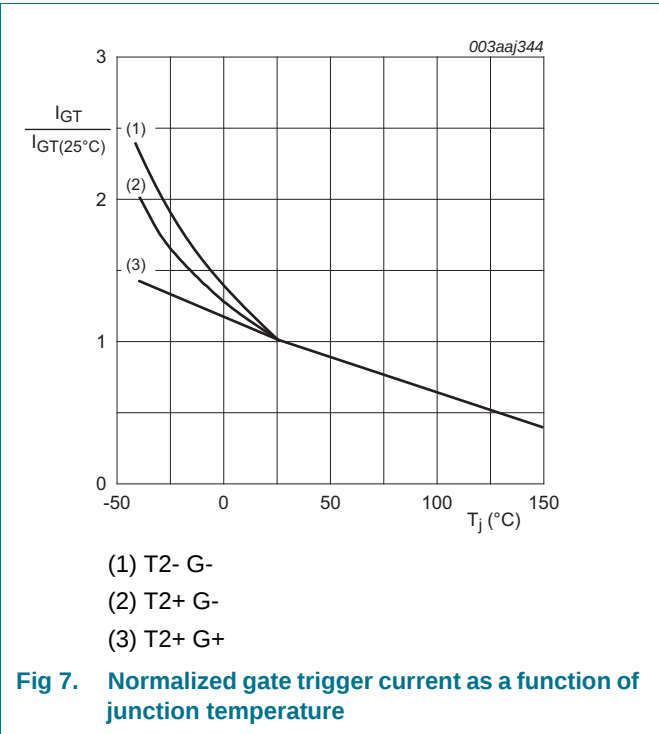
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	full cycle;see Figure 6	-	-	1.5	K/W
		half cycle;see Figure 6	-	-	2	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W



6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ }^\circ\text{C}$; see Figure 7	2	-	35	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ }^\circ\text{C}$; see Figure 7	2	-	35	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ }^\circ\text{C}$; see Figure 7	2	-	35	mA
I_L	latching current	$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ }^\circ\text{C}$; see Figure 8	-	-	50	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ }^\circ\text{C}$; see Figure 8	-	-	60	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ }^\circ\text{C}$; see Figure 8	-	-	50	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$; see Figure 9	-	-	35	mA
V_T	on-state voltage	$I_T = 15\text{ A}$; $T_j = 25\text{ }^\circ\text{C}$; see Figure 10	-	1.3	1.6	V
V_{GT}	gate trigger voltage	$V_D = 12\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$; see Figure 11	-	0.8	1.5	V
		$V_D = 400\text{ V}$; $T_j = 150\text{ }^\circ\text{C}$; see Figure 11	0.25	0.4	-	V
I_D	off-state current	$V_D = 600\text{ V}$; $T_j = 150\text{ }^\circ\text{C}$	-	0.4	2	mA
Dynamic Characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 402\text{ V}$; $T_j = 150\text{ }^\circ\text{C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit	500	-	-	V/ μs
dI_{com}/dt	rate of change of commutating current	$V_D = 400\text{ V}$; $T_j = 150\text{ }^\circ\text{C}$; $I_{T(RMS)} = 10\text{ A}$; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$; (snubberless condition); gate open circuit	8	-	-	A/ms
		$V_D = 400\text{ V}$; $T_j = 150\text{ }^\circ\text{C}$; $I_{T(RMS)} = 10\text{ A}$; $dV_{com}/dt = 10\text{ V}/\mu\text{s}$; gate open circuit	13	-	-	A/ms
		$V_D = 400\text{ V}$; $T_j = 150\text{ }^\circ\text{C}$; $I_{T(RMS)} = 10\text{ A}$; $dV_{com}/dt = 1\text{ V}/\mu\text{s}$; gate open circuit	20	-	-	A/ms



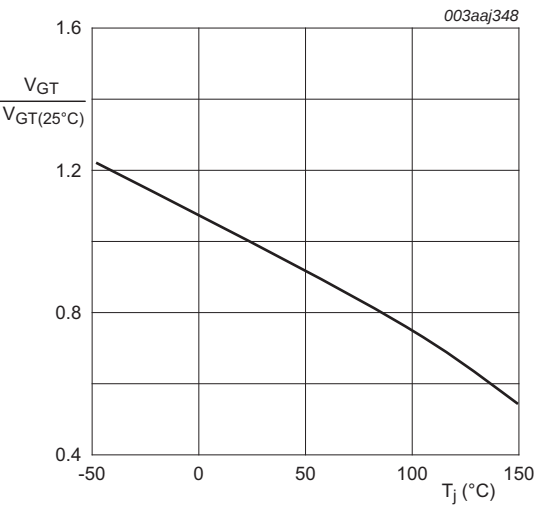


Fig 11. Normalized gate trigger voltage as a function of junction temperature

7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78

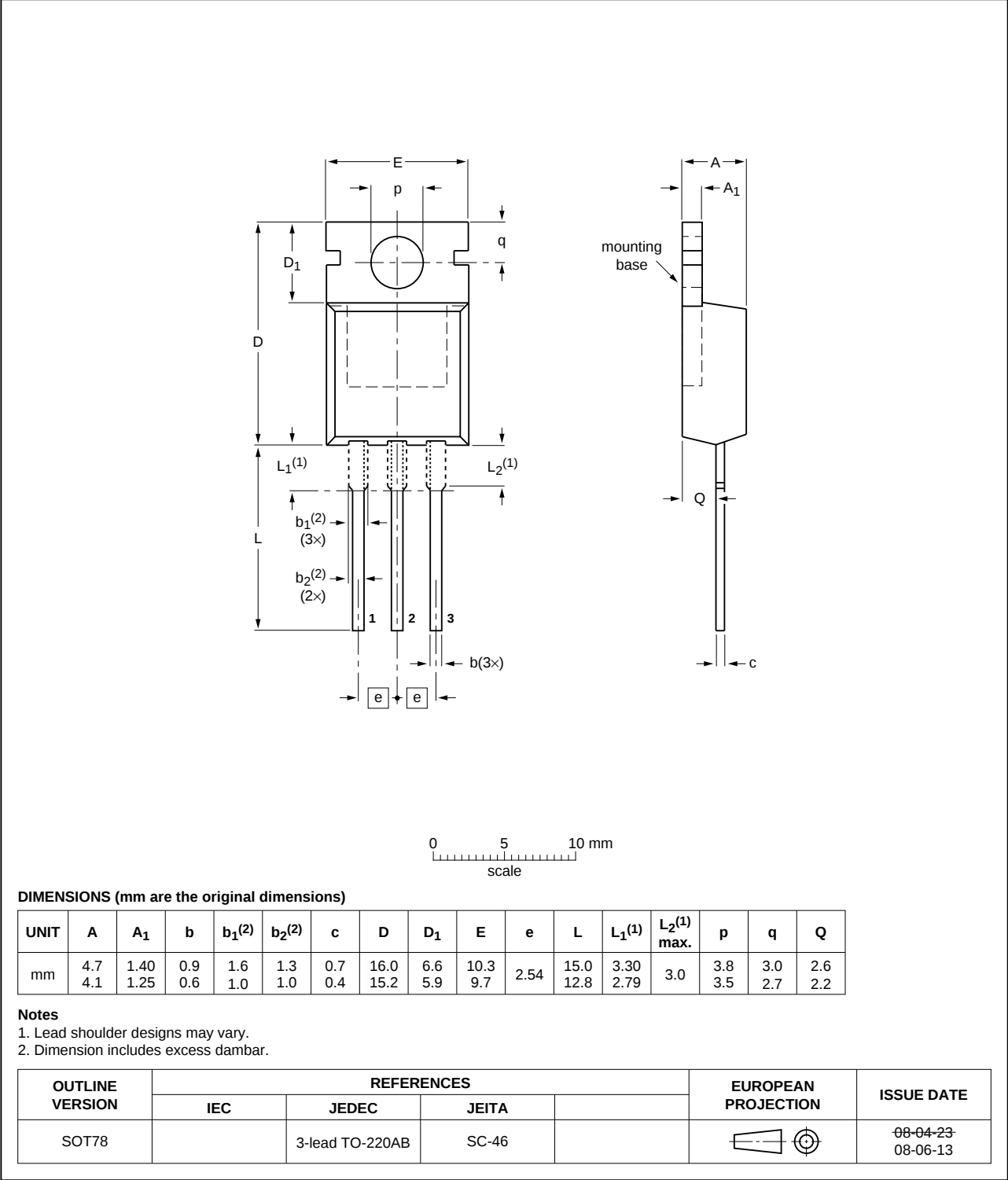


Fig 12. Package outline SOT78 (TO-220AB)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BTA410-600CT V.1	20120315	Product data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status ^{[1] [2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Date of release: 15 March 2012

Document identifier: BTA410-600CT